

PATENT  
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### **ABSTRACT OF THE DISCLOSURE**

Method for producing an antifuse in a substrate, a first interconnect being applied to the substrate, a dielectric layer being applied at an end face of the first interconnect, which end face essentially runs vertically with respect to the substrate, a second interconnect being applied in such a way that it adjoins the dielectric layer with an end face, with the result that an antifuse structure is formed.

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